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π -Conjugated Phosphasilenes Stabilized by Fused-Ring Bulky Groups

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Organic π -conjugated architectures featuring multiple bonds of the heavier main group elements¹ have attracted much attention because of their potentially useful properties and unique functions.² For example, a number of oligomers and polymers encapsulating $P=E (E = C, P)^3$ and $Si=Si^4$ bonds have been investigated, which would open the way to new elemento-organic hybrid materials. Recently, we⁵ and the Scheschkewitz group⁶ independently reported the synthesis of disilene analogues of oligo(p-phenylenevinylene)s (Si-OPVs). In our case, the fused-ring bulky Eind groups (Eind = 1,1,3,3,5,5,7,7-octaethyl-s-hydrindacen-4-yl) effectively protected the reactive Si=Si fragments, thus producing the highly coplanar arrangement of the Si-OPV framework. Notably, our 1,4-bis(disilenyl)benzene derivative shows a unique fluorescence at room temperature based on the efficient π -delocalization over the skeleton.

Although various phosphasilenes have been reported by taking advantage of the steric protection with appropriate bulky substituents, their electronic properties have rarely been explored;^{7,8} weak absorptions probably due to the $n-\pi^*$ transition have been reported only in rare cases.^{8c,g} We now report the synthesis and characterization of a series of π -conjugated phosphasilenes 1a-c and 2stabilized by the Eind groups. In our case, strong $\pi - \pi^*$ absorptions have been observed due to the highly coplanar framework incorporating the Si=P unit and the aromatic ring on the silicon atom.

Phosphasilenes 1a-c and 2 were synthesized starting from the bulky phosphine 3 (Scheme 1). The coupling reaction between lithium phosphide 4 and dibromosilanes 5a-c and subsequent removal of HBr from phosphasilanes 6a-c with 1.8diazabicyclo[5.4.0]undec-7-ene (DBU), afforded phosphasilenes 1a-c, as yellow to yellow-orange crystals in 25-65% yields. We have also isolated the orange crystals of 1,4-bis(phosphasilenyl)benzene 2 using 1,4-bis(dibromosilyl)benzene 7 in 29% yield, in which two Si=P bonds are connected by a phenylene linker. The formation of the Si=P bond was clearly confirmed by the ²⁹Si and ³¹P NMR spectra. In the ²⁹Si NMR spectra of **1a-c**, one signal was observed at 161.7–162.1 ppm as a doublet with a ${}^{1}J_{\text{SiP}}$ coupling constant of 171-174 Hz. The characteristic ³¹P NMR signal was observed at 89.2-89.7 ppm. Solid-state NMR experiments have been utilized for characterization of 2, due to its poor solubility in organic solvents. The NMR data indicated a highly symmetrical structure for 2 in the solid state, which is in agreement with the crystal structure (vide infra). The resulting phosphasilenes were found to be stable in air for months in the solid state and for a week as a dilute solution, demonstrating the efficient protection ability of the Eind groups. Each compound has high thermal

Scheme 1



stability; 1a-c have melting points of >250 °C under argon atmosphere in a sealed tube.

The crystal structures of 1a-c and 2 were revealed by X-ray analysis, as represented by 1c and 2 shown in Figure 1. The aryl and the arylene groups are entirely coplanar with the Si=P bond(s), having a P-Si-C-C torsion angle of $3.04(13)^{\circ}$ (1a), $1.1(4)^{\circ}$ (1b), $2.0(2)^{\circ}$ (1c), and $0.8(2)^{\circ}$ (2), respectively, which is well suited for the $2p_{\pi}-3p_{\pi}$ conjugation. This coplanarity is apparently attained by the two rigid Eind groups, oriented trans and perpendicular with respect to the Si=P bond, as observed in the disilene case.⁵ For 1b and 1c, the arrangement between the Si=P bond and the polycyclic aromatic substituents about the intervening Si-C bond is described as an s-cis conformational geometry in the crystals.⁹ The Si=P bond lengths (ca. 2.09-2.10 Å) are in the range of those for typical phosphasilenes.7,8



Figure 1. Molecular structures of 1c (a) and 2 (b) (50% probability level). Hydrogen atoms are omitted for clarity.

Some photophysical and electrochemical properties are summarized as follows. (1) The UV-vis spectrum of 1a shows an absorption peak at 385 nm ($\epsilon = 1.2 \times 10^4$), which is bathochromically shifted about 50 nm and 2-orders stronger relative to the longest wavelength absorption of the previously reported phosphasilenes.^{8c,g} The introduction of the 2-naphthyl (1b) and the 2-anthryl (1c) groups to the silicon atom causes further red-shifts to 405 nm $(\epsilon = 1.1 \times 10^4)$ and 430 nm (sh, $\epsilon = 1.3 \times 10^4$), respectively.

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Moreover, the absorption maximum of 2 is observed at 449 nm (ϵ = 2.2×10^4), which is 64 nm red-shifted from **1a**, indicating the extension of π -conjugation over the 1,4-bis(phosphasilenyl)benzene skeleton. (2) The extended 2 shows a weak, but distinct emission in the solid state. The emission maximum of 2 is observed at 592 nm. The large Stokes shift may be attributed to the structural change from the coplanar structure in the ground state to the twisted structure in the excited state.¹⁰ (3) The irreversible oxidation waves at +0.94 V (1a) and +0.97 V (2) as well as the quasi-reversible and the irreversible reduction waves at -2.55 V (1a) and -2.12 V (2) were observed by cyclic voltammetry, respectively, as the first experimental electrochemical studies of the phosphasilenes.

To delineate the nature of the bonding in the phosphasilenes, DFT computations at the B3LYP/6-31G** level were carried out for 1a and 2 using the Gaussian 03 program package.¹¹ The optimized structures reproduced well the X-ray crystal structures. Three pertinent MOs of 1a are shown in Figure 2. While the HOMO of **1a** is primarily represented by the $3p_{\pi}(Si-P)$ orbital, the LUMO contribution involves the substantial of the $3p_{\pi}^{*}(Si-P)-2p_{\pi}^{*}(phenyl)$ conjugation. The lower-lying HOMO-1 involves the $3n-2p_{\pi}$ conjugation due to the lone pair on the phosphorus atom and the π -orbital on the Eind benzene ring; the maximum orbital interaction of these two orbitals is attained by the perpendicularly-fixed Eind group. Calculations for the π -extended 2 have demonstrated that the LUMO level is lowered [-1.552 (1a) and -2.108 (2) eV], thus keeping the HOMO levels nearly constant [-5.141 (1a) and -5.137 (2) eV], in agreement with the orbital shapes for 1a and the electrochemical experimental results mentioned above.



Figure 2. Selected molecular orbitals of 1a (top view).

The wavelengths were calculated to be 364 (1a) and 456 (2) nm based on TD-DFT calculations, comparable to the observed values. The absorption at 364 nm of **1a** is assignable to the mixed version of the HOMO \rightarrow LUMO (π - π *) and HOMO-1 \rightarrow LUMO ((n + π of Eind benzene) $-\pi^*$) transitions with almost equal weighting. In contrast, the absorption at 456 nm of 2 is mainly assigned to the HOMO→LUMO (π - π *) transition.

In conclusion, we have established for the first time that the Si=P bond can conjugate with the carbon π -electron system by introduction of a variety of aryl substituents on the silicon atom and the use of the Eind groups as protecting groups. Further work to clarify the promising coordination abilities of these phosphasilenes is currently underway.

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Supporting Information Available: Experimental details, crystallographic data of 1a-c and 2 (CIF), details for calculations of 1a and 2, and full listing for ref 11. This material is available free of charge via Internet at http://pubs.acs.org.

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